AOT10T60P/AOB10T60P/AOTF10T60P

600V,10A N-Channel MOSFET

General Description

- Trench Power AlphaMOS-II technology
- Low $R_{DS(ON)}$
- Low Ciss and Crss
- High Current Capability
- RoHS and Halogen Free Compliant

Applications

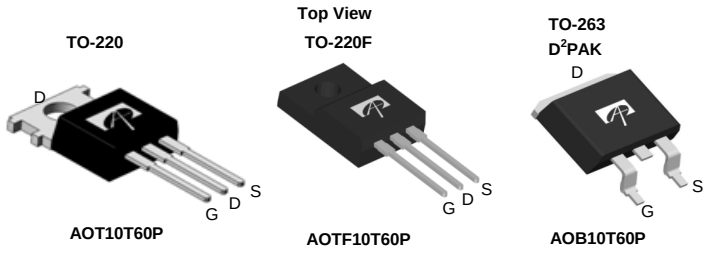
- General Lighting for LED and CCFL
- AC/DC Power supplies for Industrial, Consumer, and Telecom

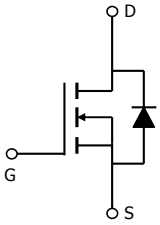
Product Summary

V_{DS} @ $T_{j,max}$	700V
I_{DM}	40A
$R_{DS(ON),max}$	< 0.7Ω
$Q_{g,typ}$	26nC
E_{oss} @ 400V	3.5µJ

100% UIS Tested
100% R_g Tested

RoHS Compliant





Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOT10T60PL	TO-220 Green	Tube	1000
AOB10T60PL	TO-263 Green	Tape & Reel	800
AOTF10T60P	TO-220F Pb Free	Tube	1000
AOTF10T60PL	TO-220F Green	Tube	1000

Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	AOT(B)10T60P	AOTF10T60P	AOTF10T60PL	Units
Drain-Source Voltage		V_{DS}	600			V
Gate-Source Voltage		V_{GS}	±30			V
Continuous Drain Current	T_C=25℃	I_D	10	10*	10*	A
	T_C=100℃		6.6	6.6*	6.6*	
Pulsed Drain Current [C]		I_{DM}	40			
Avalanche Current [C] L=1mH		I_{AR}	10			A
Repetitive avalanche energy [C]		E_{AR}	50			mJ
Single pulsed avalanche energy [G]		E_{AS}	480			mJ
MOSFET dv/dt ruggedness		dv/dt	50			V/ns
Peak diode recovery dv/dt [J]			15			
Power Dissipation [B]	T_C=25℃	P_D	208	43	33	W
	Derate above 25℃		1.7	0.3	0.26	W/℃
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150			℃
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300			℃

Thermal Characteristics

Parameter	Symbol	AOT(B)10T60P	AOTF10T60P	AOTF10T60PL	Units
Maximum Junction-to-Ambient [A,D]	$R_{\theta JA}$	65	65	65	℃/W
Maximum Case-to-sink [A]	$R_{\theta CS}$	0.5	--	--	℃/W
Maximum Junction-to-Case	$R_{\theta JC}$	0.6	2.9	3.8	℃/W

* Drain current limited by maximum junction temperature.

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V, T_J=25°C	600			V
		I_D=250µA, V_{GS}=0V, T_J=150°C		700		
BV_{DSS} /ΔTJ	Breakdown Voltage Temperature Coefficient	I_D=250µA, V_{GS}=0V		0.56		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=600V, V_{GS}=0V			1	µA
		V_{DS}=480V, T_J=125°C			10	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±30V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=5V, I_D=250µA	3	4.3	5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=5A		0.58	0.7	Ω
g_{FS}	Forward Transconductance	V_{DS}=40V, I_D=5A		8.8		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.74	1	V
I_S	Maximum Body-Diode Continuous Current				10	A
I_{SM}	Maximum Body-Diode Pulsed Current [C]				40	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=100V, f=1MHz		1595		pF
C_{oss}	Output Capacitance			56		pF
$C_{o(er)}$	Effective output capacitance, energy related [H]	V_{GS}=0V, V_{DS}=0 to 480V, f=1MHz		42		pF
$C_{o(tr)}$	Effective output capacitance, time related [I]			74		pF
C_{rss}	Reverse Transfer Capacitance	V_{GS}=0V, V_{DS}=100V, f=1MHz		11		pF
R_g	Gate resistance	f=1MHz		1.7		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=480V, I_D=10A		26	40	nC
Q_{gs}	Gate Source Charge			8.1		nC
Q_{gd}	Gate Drain Charge			8.2		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=300V, I_D=10A, R_G=25Ω		42		ns
t_r	Turn-On Rise Time			54		ns
$t_{D(off)}$	Turn-Off DelayTime			52		ns
t_f	Turn-Off Fall Time			24		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=10A,dI/dt=100A/µs,V_{DS}=100V		497		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=10A,dI/dt=100A/µs,V_{DS}=100V		7.3		µC

A. The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A=25°C.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C, Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 ms pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C. The SOA curve provides a single pulse ratin g.

G. L=60mH, I_{AS}=4A, V_{DD}=150V, R_G=25Ω, Starting T_J=25°C.

H. $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.

I. $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.

J. I_{SD}≤I_D, di/dt≤200A/µs, V_{DD}=400V, T_J≤$T_{J(MAX)}$.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

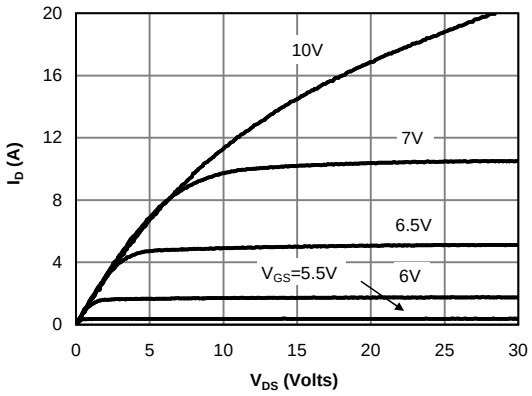


Figure 1: On-Region Characteristics

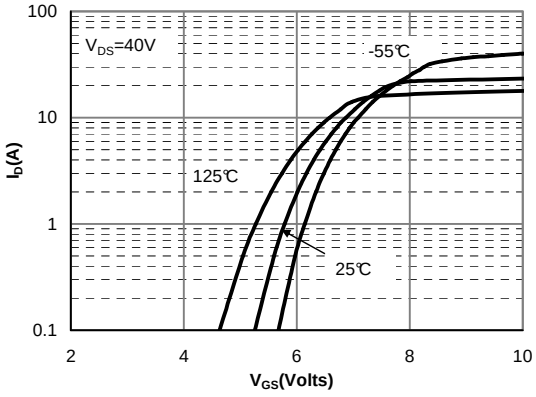


Figure 2: Transfer Characteristics

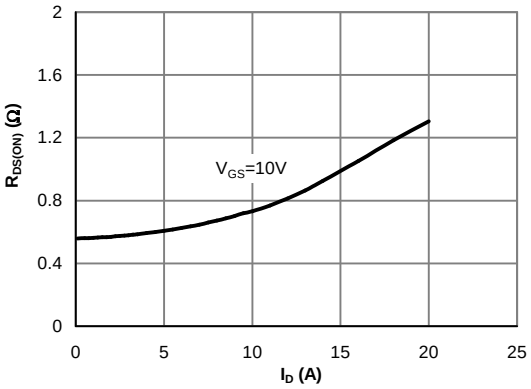


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

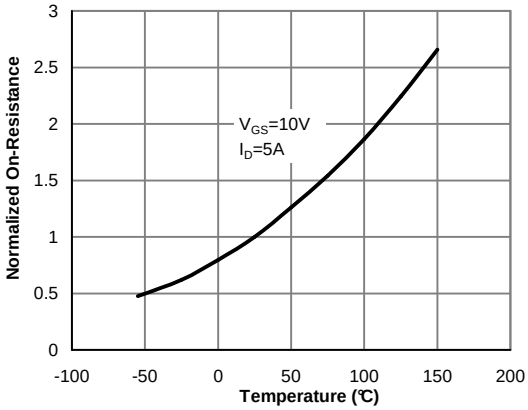


Figure 4: On-Resistance vs. Junction Temperature

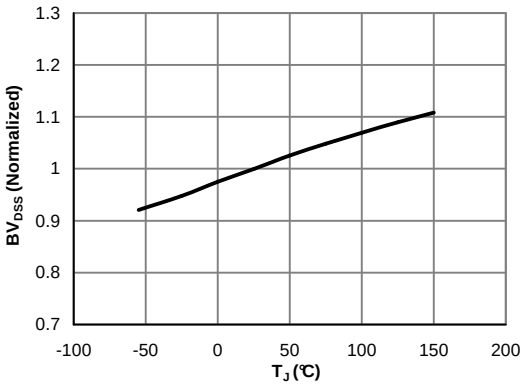


Figure 5: Break Down vs. Junction Temparature

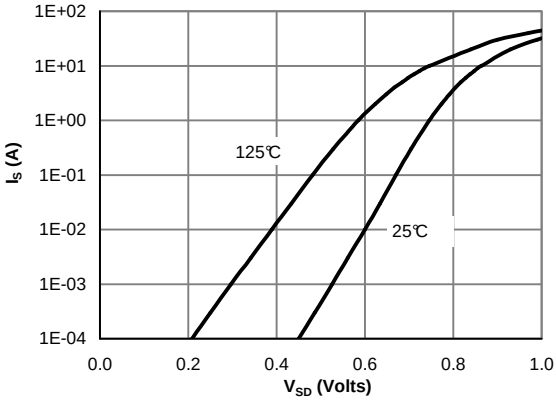


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

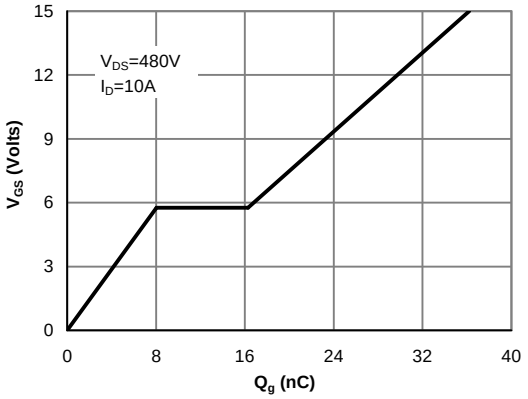


Figure 7: Gate-Charge Characteristics

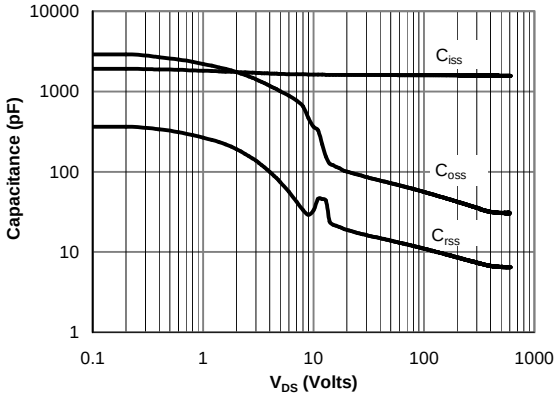


Figure 8: Capacitance Characteristics

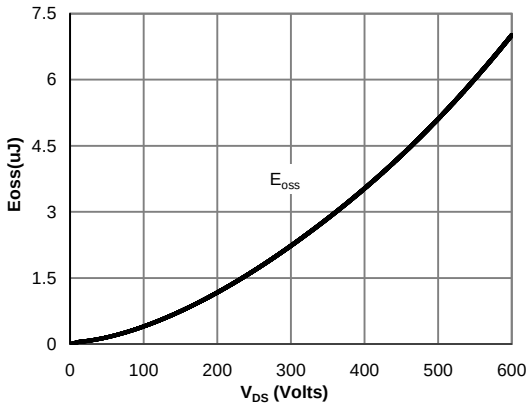


Figure 9: Coss stored Energy

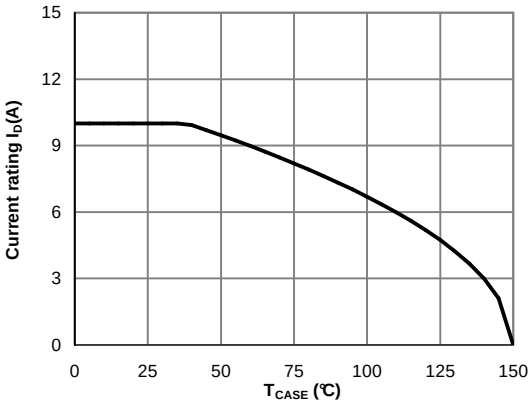


Figure 10: Current De-rating (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

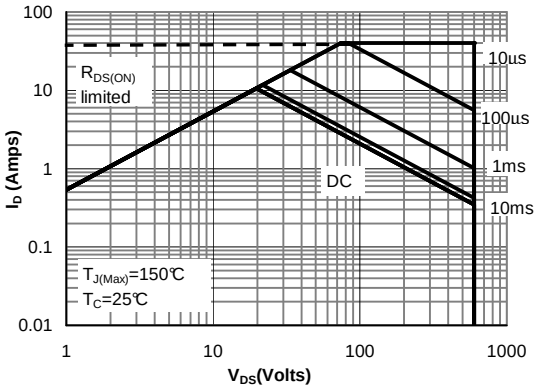


Figure 11: Maximum Forward Biased Safe Operating Area for TO-220/TO-263 (Note F)

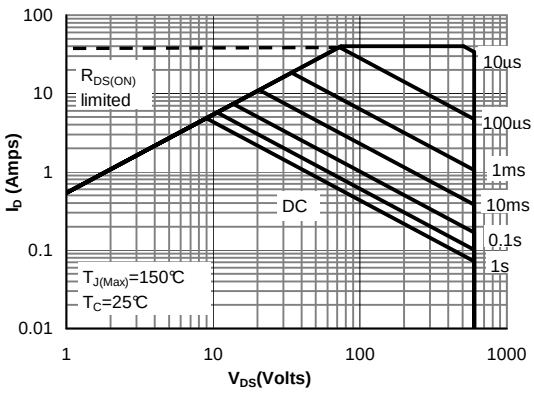


Figure 12: Maximum Forward Biased Safe Operating Area for TO-220F Pb Free (Note F)

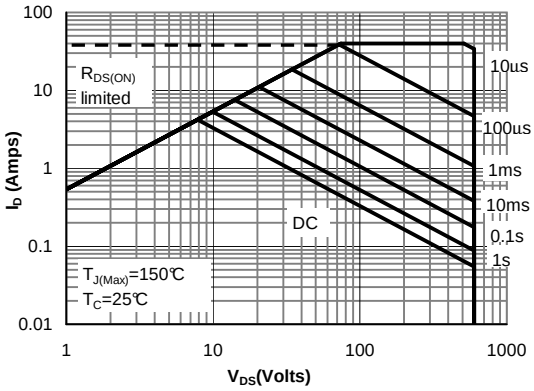


Figure 13: Maximum Forward Biased Safe Operating Area for TO-220F Green (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

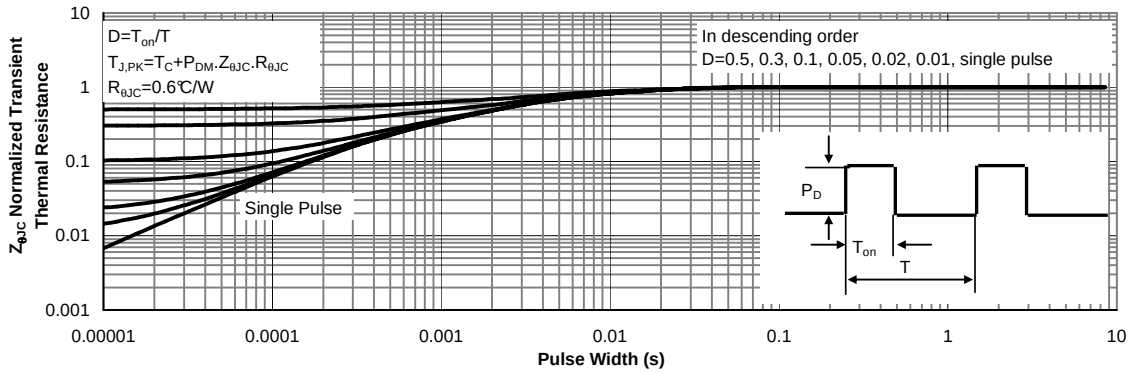


Figure 14: Normalized Maximum Transient Thermal Impedance for TO-220/TO-263 (Note F)

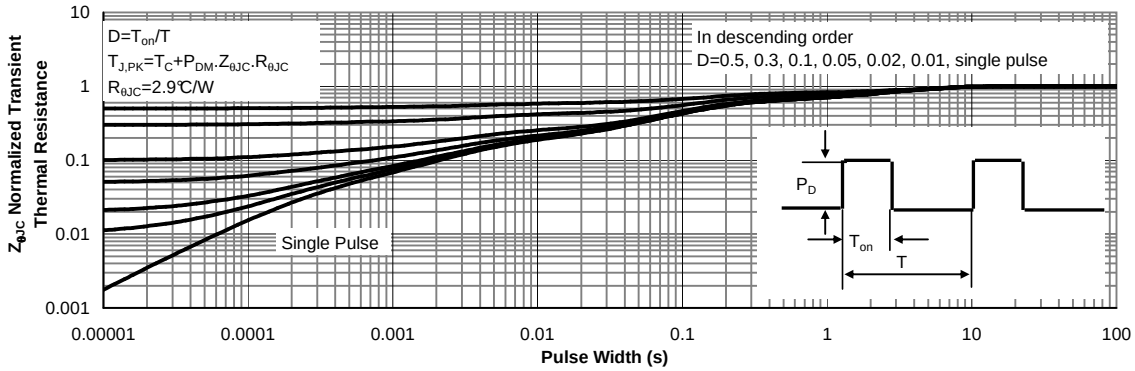


Figure 15: Normalized Maximum Transient Thermal Impedance for TO-220F Pb Free (Note F)

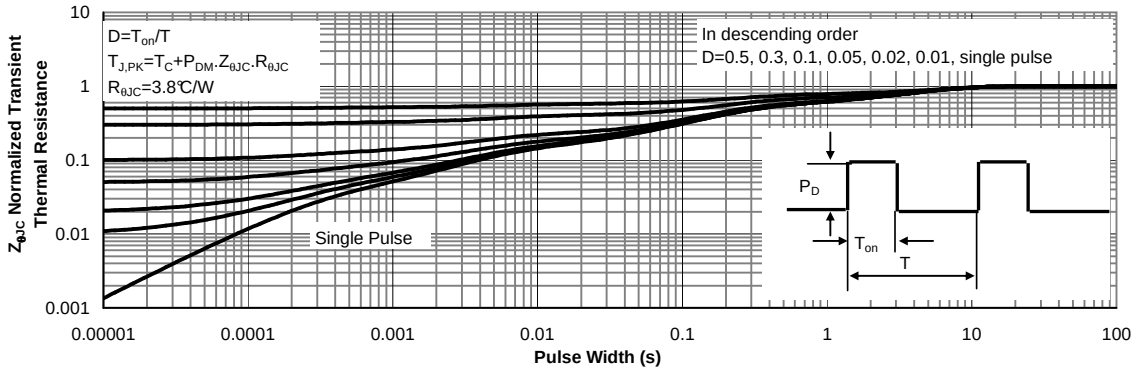
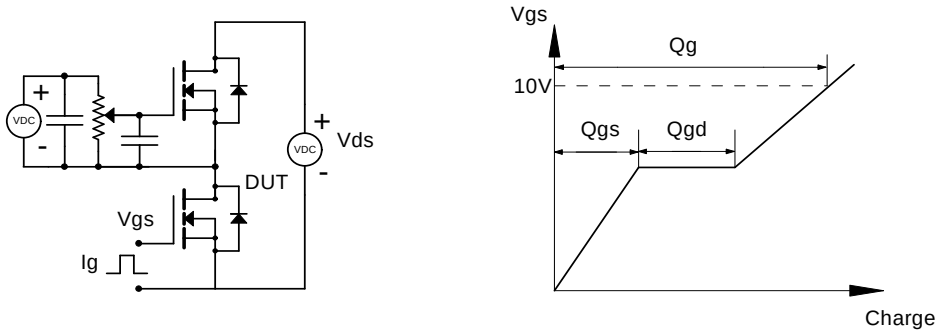
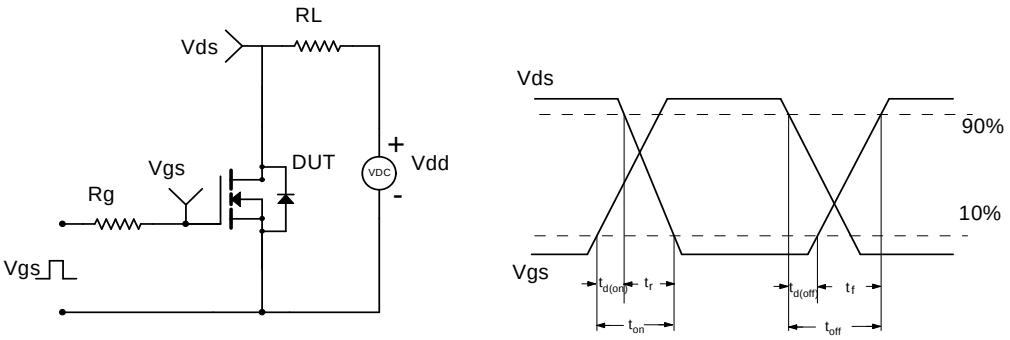


Figure 16: Normalized Maximum Transient Thermal Impedance for TO-220F Green (Note F)

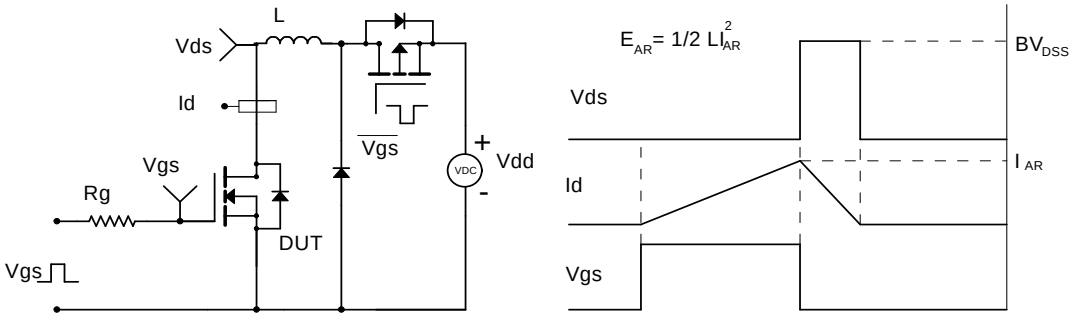
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms